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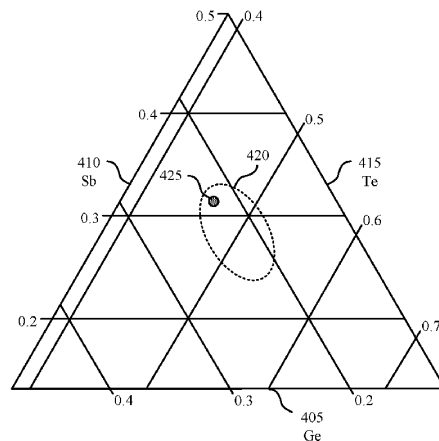


FIG. 4

(57) Abstract: Methods, systems, and devices for operating memory cell(s) using transition metal doped GST are described. As discussed herein, a composition including germanium (Ge), antimony (Sb), tellurium (Te), and at least one of yttrium (Y) and scandium (Sc) may be used as a memory element in a memory cell. For example, a memory element may include a composition having Ge in an amount ranging from 15 to 35 atomic percent (at.%) of the composition, Sb in an amount less than or equal to 50 at.% of the composition, Te in an amount greater than or equal to 40 at.% of the composition, and at least one of Y and Sc in an amount ranging from 0.15 to 10 at.% of the composition.

[Continued on next page]

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